

ROITHNER LASERTECHNIK GMBH

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LED36-SMD5

TECHNICAL DATA



Mid-Infrared Light Emitting Diode, SMD

Light Emitting Diodes with central wavelength 3.65 μ m series are based on heterostructures grown on InAs substrates by MOCVD. InAsSb is used in the active layer. Wide band gap solid solutions InAsSbP with P content 50% are used for good electron confinement.

LED36-SMD5 has a stable ouput power and a lifetime more then 80000 hours.

Features

Structure: InAsSb/InAsSbP
Peak Wavelength: typ. 3.65 μm

Optical Ouput Power: typ. 30 µW qCW

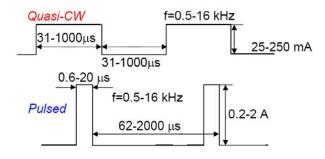
Package: SMD 5x5 mm



Specifications

ltem	Condition		Rating		Unit
item	Condition	Min.	Тур.	Max.	Unit
Peak Wavelength	T=300 K	3.60	3.65	3.70	μm
FWHM	150 mA CW	0.40	0.50	0.60	μm
Quasi-CW Optical Power	200 mA qCW	20	30	40	μW
Pulsed Optical Power	1 A	180	200	220	μW
Switching Time	T=300 K	10	20	30	ns
Operation Voltage	200 mA qCW				V
Operating Temperature		-240 +	50		°C
Emitting Area		300x300)		μm
Soldering Temperature		180			ပ္
Package	SMD type package 5x5 mm based on high thermal conductivity ceramics				

Operating Regime



Quasi-CW

- Maximum current 220 mA
- Recommended current 150-200mA

Pulsed

 Maximum current 1 A (puls lenght 500 ns, repetition rate 2kHz)

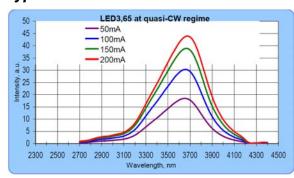


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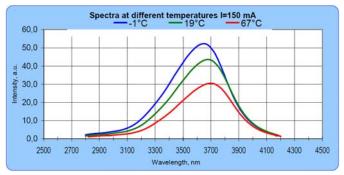
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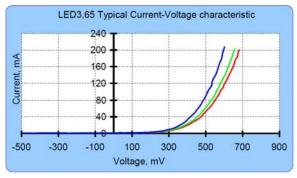


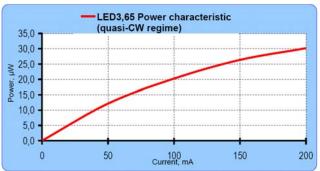
Typical Performance Curves



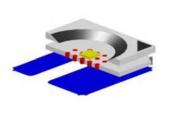
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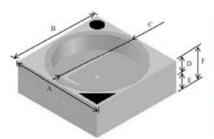






Package





ITEM	Symbol	Rule	
Basic Outline	A	5.0± 0.1mm	
Basic Outline	В	5.0± 0.1mm	
Cavity size	С	Max 4.2Φ	
Top layer	D	Min 0.4mm	
Bottom layer	E	Min 0.4mm	
Thickness	F	Max 2mm	

- · Tiny package for surface mounting
- Anode and cathode are led to the metalized areas on the back side of the ceramic surface
- Material Low Temperature Co-fired Ceramic (LTCC):
 - thermal conductivity 25 W/mK
 - thermoresistance 8 °C/W